

SILICON POWER TRANSISTOR 2SA1742

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1742 is a power transistor developed for high-speed switching and features a high hFE at low VCE(sat). This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

FEATURES

- High hre and low $V_{CE(sat)}$: hre \geq 100 MIN. @ $V_{CE} = -2.0$ V, Ic = -1.5 A $V_{CE(sat)} \geq -0.3$ V MAX. @ Ic = -4.0 V, IB = -0.2 A
- Full-mold package that does not require an insulating board or bushing

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-100	٧
Collector to emitter voltage	VCEO		-60	٧
Emitter to base voltage	VEBO		-7.0	٧
Collector current (DC)	Ic(DC)		-7.0	Α
Collector current (pulse)	IC(pulse)	PW \leq 300 μ s,	-14	Α
		duty cycle ≤ 10%		
Base current (DC)	I _{B(DC)}		-3.5	Α
Total power dissipation	Р⊤	Tc = 25°C	30	W
		T _A = 25°C	2.0	W
Junction temperature	Tj		150	°C
Storage temperature	T _{stg}		-55 to +150	°C

ORDERING INFORMATION

Part No.	Package
2SA1742	Isolated TO-220

(Isolated TO-220)



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ELECTRICAL CHARACTERISTICS (TA = 25°C)

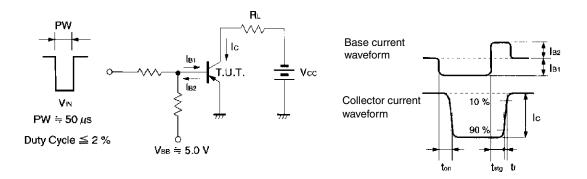
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	Ic = −4.0 V, I _B = −0.4 A, L = 1 mH	-60			V
	VCEX(SUS)	Ic = -4.0 A, I _{B1} = $-I$ _{B2} = -0.4 A, V _{BE(OFF)} = 1.5 V, L = 180 μ H, clamped	-60			V
Collector cutoff current	Ісво	Vcb = -60 V, IE = 0 A			-10	μΑ
	ICER	$V_{CE} = -60 \text{ V}, \text{ R}_{BE} = 50 \Omega, \text{ T}_{A} = 125 ^{\circ}\text{C}$			-1.0	mA
	ICEX1	$V_{CE} = -60 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V}$			-10	μΑ
	ICEX2	$V_{CE} = -60 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V},$ $T_A = 125^{\circ}\text{C}$			-1.0	mA
Emitter cutoff current	ІЕВО	V _{EB} = -5.0 V, I _C = 0 A			-10	μΑ
DC current gain	h _{FE1}	$V_{CE} = -2.0 \text{ V}, I_{C} = -0.7 \text{ A}^{Note}$	100			
	hFE2	$V_{CE} = -2.0 \text{ V}, I_{C} = -1.5 \text{ A}^{Note}$	100		400	
	h _{FE3}	$V_{CE} = -2.0 \text{ V}, I_{C} = -4.0 \text{ A}^{Note}$	60			
Collector saturation voltage	V _{CE(sat)1}	$Ic = -4.0 \text{ A}, IB = -0.2 \text{ A}^{\text{Note}}$			-0.3	V
	V _{CE(sat)2}	$Ic = -6.0 \text{ A}, IB = -0.3 \text{ A}^{\text{Note}}$			-0.5	V
Base saturation voltage	V _{BE(sat)1}	$I_C = -4.0 \text{ A}, I_B = -0.2 \text{ A}^{\text{Note}}$			-1.2	V
	V _{BE(sat)2}	$Ic = -6.0 \text{ A}, IB = -0.3 \text{ A}^{\text{Note}}$			-1.5	V
Collector capacitance	Cob	$V_{CB} = -10 \text{ V}, I_E = 0 \text{ A}, f = 1.0 \text{ MHz}$		180		pF
Gain bandwidth product	f⊤	$V_{CB} = -10 \text{ V}, I_{C} = -1.0 \text{ A}$		40		MHz
Turn-on time	ton	Ic = -4.0 A, R _L = 12.5 Ω,			0.3	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.2 \text{ A}, \text{ Vcc } \cong -50 \text{ V}$			1.5	μs
Fall time	t f	Refer to the test circuit.			0.3	μs

Note Pulse test PW \leq 350 μ s, duty cycle \leq 2%

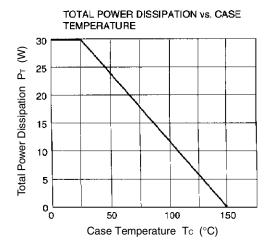
hfe CLASSIFICATION

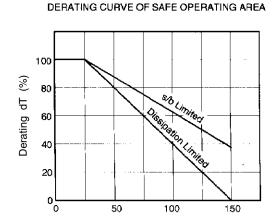
Marking	М	L	K
h _{FE2}	100 to 200	150 to 300	200 to 400

SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

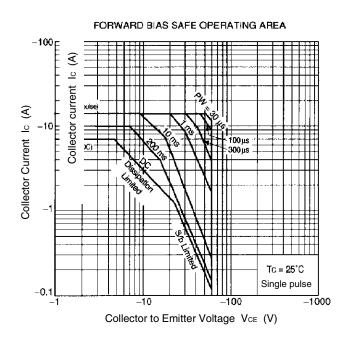


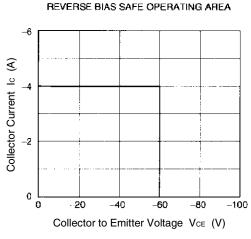
TYPICAL CHARACTERISTICS (TA = 25°C)

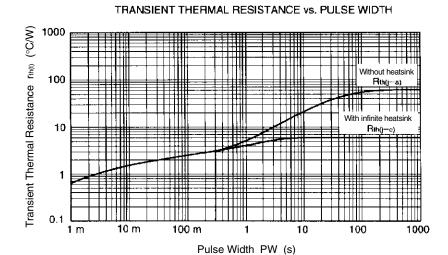




Case Temperature Tc (°C)

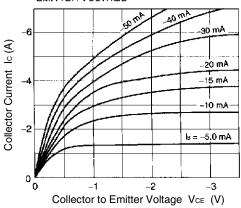




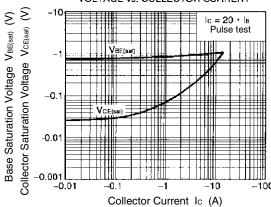


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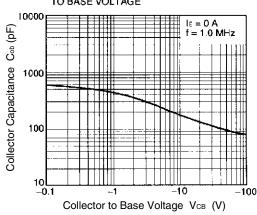




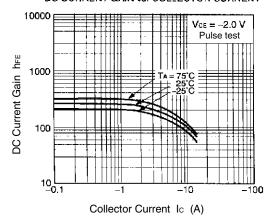
COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



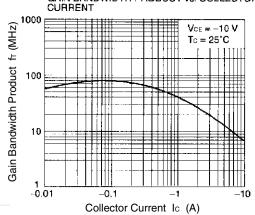
OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



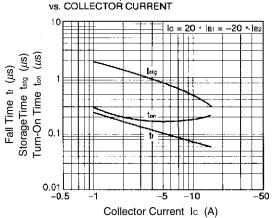
DC CURRENT GAIN vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



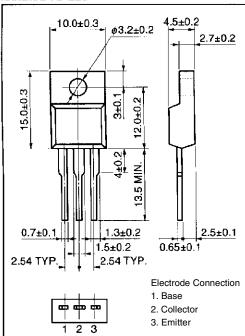
TURN ON TIME, STORAGE TIME AND FALL TIME





PACKAGE DRAWING (UNIT: mm)

Isolated TO-220



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